



PNP 2N6051

12A Complementary Silicon **Power Transistors** 60V - 100V

150W

Description:

Designed for general-purpose power amplifier and low frequency switching applications

Features:

- Monolithic construction with bult-in base-emitter shunt resistors
- High DC current gain hFE = 3,500 (typical) at Ic = 5A



TO-3

Maximum Ratings

Characteristic	Symbol	2N6051	Unit	
Collector-Emitter Voltage	V _{CEO}	00		
Collector-Base Voltage	V _{CBO}	80	V	
Emitter-Base Voltage	V _{EBO}	5		
Collector Current -Continuous -Peak	I _C	12 20	А	
Base Current	I _B	0.2		
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	150 0.857	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +200	°C	

Thermal Characteristics

Characteristic	Symbol	Max.	Unit
Thermal Resistance Junction to Case	Rejc	1.17	°C/W



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Electrical Characteristics (TC = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
Off Characteristics				
Collector-Emitter Sustaining Voltage (1) $(I_C = 100 \text{mA}, I_B = 0)$	V _{CEO (sus)}	80	-	V
Collector Cut off Current (V _{CE} = 40V, I _B = 0)	I _{CEO}	-	1	
Collector Cut off Current $(V_{CE} = Rated \ V_{CEO}, \ V_{BE \ (off)} = 1.5V)$ $(V_{CE} = Rated \ V_{CEO}, \ V_{BE \ (off)} = 1.5V, \ T_{C} = 150^{\circ}C)$	I _{CEX}	-	0.5 5	mA
Emitter Cut off Current $(V_{EB} = 5V, I_C = 0)$	ı	-	2	

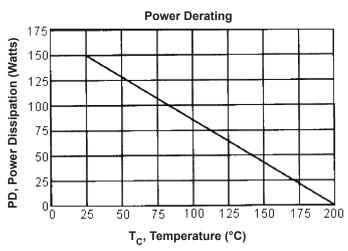
On Characteristics (1)

DC Current Gain ($I_C = 6A$, $V_{CE} = 3V$) ($I_C = 12A$, $V_{CE} = 3V$)	h _{FE}	750 100	18,000	-
Collector-Emitter Saturation Voltage ($I_C = 6A$, $I_B = 24mA$) ($I_C = 12A$, $I_B = 120mA$)	V _{CE (sat)}	-	2 3	
Base-Emitter On Voltage ($I_C = 6A$, $V_{CE} = 3V$)	V	-	2.8	V
Base-Emitter Saturation Voltage $(I_C = 12A, I_B = 120mA)$	V	-	4	

Dynamic Characteristics

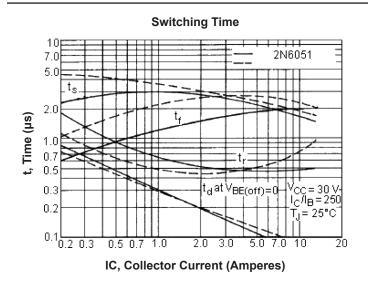
Current-Gain-Bandwidth Product (2) ($I_C = 500$ mA, $V_{CE} = 3$ V, $f = 1$ MHz)	f	4	-	MHz
Small-Signal Current Gain (I _C = 5A, V _{CE} = 3V, f = 1.0kHz)	h	300	-	IVI⊓∠

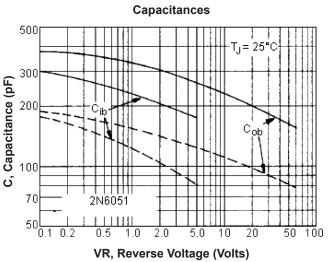
- (1) Pulse Test : Pulse Width ≤300µs, Duty Cycle ≤2.0%.
- (2) fT = | hfe | ftest.

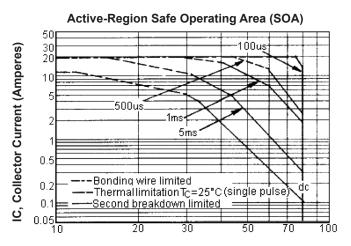








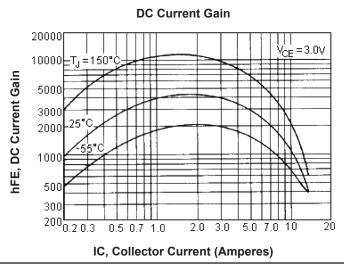


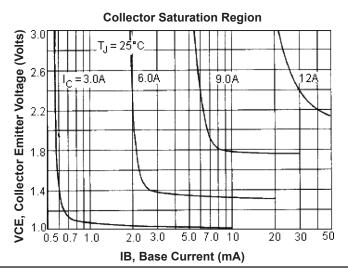


There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on TJ (PK) = 200°C; TC is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided TJ (PK) ≤200°C. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

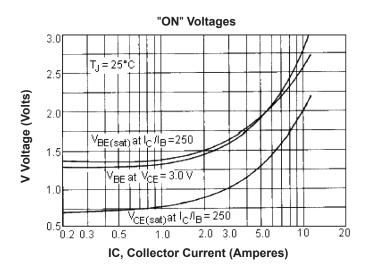




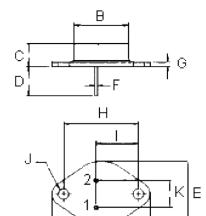








TO-3



А

1. Base
2. Emitter
Collector (Case)

Ρ

Dimensions	Min.	Max.
А	38.75	39.96
В	19.28	22.23
С	7.96	9.28
D	11.18	12.19
E	25.2	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.9	30.4
I	16.64	17.3
J	3.88	4.36
K	10.67	11.18

Dimensions : Millimetres

Part Number Table

Description	Part Number	
Darlington Transistor, TO-3	2N6051	

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